

FMS7G20US60S

Compact & Complex Module

Features

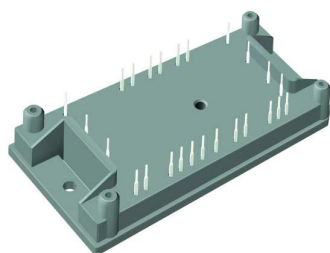
- Short Circuit Rated $10\mu\text{s}$ @ $T_C = 100^\circ\text{C}$, $V_{GE} = 15\text{V}$
- High Speed Switching
- Low Saturation Voltage : $V_{CE(sat)} = 2.1\text{ V @ } I_C = 20\text{A}$
- High Input Impedance
- Built-in Brake & 1 Phase Rectifier Circuit
- Fast & Soft Anti-Parallel FWD
- Built-in NTC Thermistor

Applications

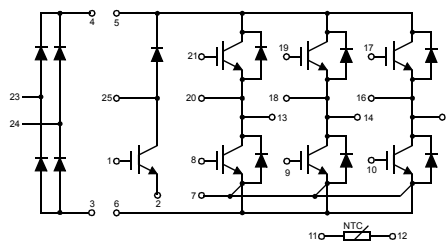
- AC & DC Motor Controls
- General Purpose Inverters
- Robotics
- Servo Controls

Description

Fairchild IGBT Power Module provides low conduction and switching losses as well as short circuit ruggedness. It's designed for the applications such as motor control and general inverters where short-circuit ruggedness is required.



Package Code : 25PM-AA



Internal Circuit Diagram

Absolute Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted

	Symbol	Description	FMS7G20US60S	Units
Inverter & Brake	V_{CES}	Collector-Emitter Voltage	600	V
	V_{GES}	Gate-Emitter Voltage	± 20	V
	I_C	Collector Current @ $T_C = 80^\circ\text{C}$	20	A
	$I_{CM(1)}$	Pulsed Collector Current	40	A
	I_F	Diode Continuous Forward Current @ $T_C = 80^\circ\text{C}$	20	A
	I_{FM}	Diode Maximum Forward Current	40	A
	P_D	Maximum Power Dissipation @ $T_C = 25^\circ\text{C}$	89	W
	T_{SC}	Short Circuit Withstand Time @ $T_C = 100^\circ\text{C}$	10	μs
Converter	V_{RRM}	Repetitive Peak Reverse Voltage	1600	V
	I_O	Average Output Rectified Current	30	A
	I_{FSM}	Surge Forward Current @ 1Cycle at 60Hz, Peak value Non-Repetitive	300	A
	i^2t	Energy pulse @ 1Cycle at 60Hz	369	A^2s
Common	T_J	Operating Junction Temperature	-40 to +150	$^\circ\text{C}$
	T_{STG}	Storage Temperature Range	-40 to +125	$^\circ\text{C}$
	V_{ISO}	Isolation Voltage @ AC 1minute	2500	V
Mounting Torque		Mounting part Screw @ M4	2.0	N·m

Notes :

(1) Repetitive rating : Pulse width limited by max. junction temperature

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FMS7G20US60S	FMS7G20US60S	25PM-AA	--	--	--

(2) TMC2 Reliability test was done under $-45^\circ\text{C} \sim 125^\circ\text{C}$

Electrical Characteristics of IGBT @ Inverter $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
Off Characteristics						
BV _{CES}	Collector-Emitter Breakdown Voltage	V _{GE} = 0V, I _C = 250μA	600	--	--	V
ΔB _{V_{CES}} /ΔT _J	Temperature Coeff. of Breakdown Voltage	V _{GE} = 0V, I _C = 1mA	--	0.6	--	V/°C
I _{CES}	Collector Cut-Off Current	V _{CE} = V _{CES} , V _{GE} = 0V	--	--	250	μA
I _{GES}	Gate - Emitter Leakage Current	V _{GE} = V _{GES} , V _{CE} = 0V	--	--	± 100	nA
On Characteristics						
V _{GE(th)}	Gate - Emitter Threshold Voltage	I _C = 20mA, V _{CE} = V _{GE}	5.0	6.5	8.5	V
V _{CE(sat)}	Collector to Emitter Saturation Voltage	I _C = 20A, V _{GE} = 15V	--	2.1	2.7	V
Dynamic Characteristics						
C _{ies}	Input Capacitance	V _{CE} = 30V, V _{GE} = 0V, f = 1MHz	--	1277	--	pF
C _{oes}	Output Capacitance		--	98	--	pF
C _{res}	Reverse Transfer Capacitance		--	21	--	pF
Switching Characteristics						
t _{d(on)}	Turn-On Delay Time	V _{CC} = 300 V, I _C = 20A, R _G = 10Ω, V _{GE} = 15V, Inductive Load, T _C = 25°C	--	65	130	ns
t _r	Rise Time		--	100	200	ns
t _{d(off)}	Turn-Off Delay Time		--	80	160	ns
t _f	Fall Time		--	100	200	ns
E _{on}	Turn-On Switching Loss		--	0.45	--	mJ
E _{off}	Turn-Off Switching Loss	--	0.42	--	mJ	
t _{d(on)}	Turn-On Delay Time	V _{CC} = 300 V, I _C = 20A, R _G = 10Ω, V _{GE} = 15V, Inductive Load, T _C = 125°C	--	70	140	ns
t _r	Rise Time		--	100	200	ns
t _{d(off)}	Turn-Off Delay Time		--	110	220	ns
t _f	Fall Time		--	210	350	ns
E _{on}	Turn-On Switching Loss		--	0.5	--	mJ
E _{off}	Turn-Off Switching Loss		--	0.72	--	mJ
T _{sc}	Short Circuit Withstand Time		V _{CC} = 300 V, V _{GE} = 15V @ T _C = 100°C	10	--	--
Q _g	Total Gate Charge	V _{CE} = 300 V, I _C = 20A, V _{GE} = 15V	--	55	65	nC
Q _{ge}	Gate-Emitter Charge		--	10	15	nC
Q _{gc}	Gate-Collector Charge		--	20	30	nC

Electrical Characteristics of DIODE @ Inverter $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions		Min.	Typ.	Max.	Units
V _{FM}	Diode Forward Voltage	I _F = 20A	T _C = 25°C	--	1.9	2.8	V
			T _C = 100°C	--	2.0	--	
t _{rr}	Diode Reverse Recovery Time	I _F = 20A di / dt = 40 A/μs	T _C = 25°C	--	75	150	ns
			T _C = 100°C	--	110	--	
I _{rr}	Diode Peak Reverse Recovery Current		T _C = 25°C	--	1.3	2.6	A
			T _C = 100°C	--	1.8	--	
Q _{rr}	Diode Reverse Recovery Charge		T _C = 25°C	--	50	195	nC
			T _C = 100°C	--	100	--	

Electrical Characteristics of DIODE @ Converter $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions		Min.	Typ.	Max.	Units
V_{FM}	Diode Forward Voltage	$I_F = 30\text{A}$	$T_C = 25^\circ\text{C}$	--	1.1	1.5	V
			$T_C = 100^\circ\text{C}$	--	1.0	--	
I_{RRM}	Repetitive Reverse Current	$V_R = V_{RRM}$	$T_C = 25^\circ\text{C}$	--	--	8	mA
			$T_C = 100^\circ\text{C}$	--	5	--	

Thermal Characteristics

	Symbol	Parameter	Typ.	Max.	Units
Inverter	$R_{\theta JC}$	Junction-to-Case (IGBT Part, per 1/6 Module)	--	1.4	$^\circ\text{C}/\text{W}$
	$R_{\theta JC}$	Junction-to-Case (DIODE Part, per 1/6 Module)	--	2.3	$^\circ\text{C}/\text{W}$
Brake	$R_{\theta JC}$	Junction-to-Case (IGBT Part)	--	1.4	$^\circ\text{C}/\text{W}$
	$R_{\theta JC}$	Junction-to-Case (DIODE Part)	--	2.3	$^\circ\text{C}/\text{W}$
Converter	$R_{\theta JC}$	Junction-to-Case (DIODE Part, per 1/6 Module)	--	1.3	$^\circ\text{C}/\text{W}$
Weight		Weight of Module	60	--	g

NTC Thermistor Characteristics

	Symbol	Parameter	Tol.	Typ.	Units
Thermistor	R25	Rated Resistance @ $T_c = 25^\circ\text{C}$	+/- 5 %	4.7	$\text{K}\Omega$
	B(25/100)	B - Value	+/- 3 %	3530	

Typical Performance Characteristics

Figure 1. Typical Output Characteristics

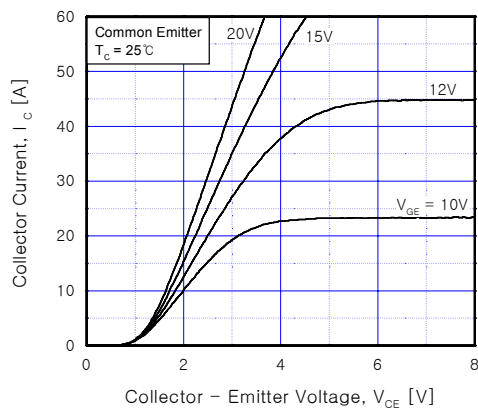


Figure 2. Typical Saturation Voltage Characteristics

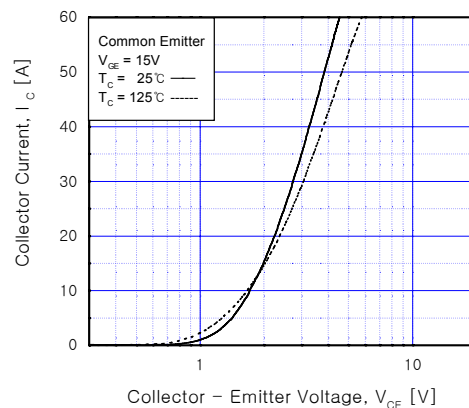


Figure 3. Saturation Voltage vs. Case Temperature at Variant Current Level

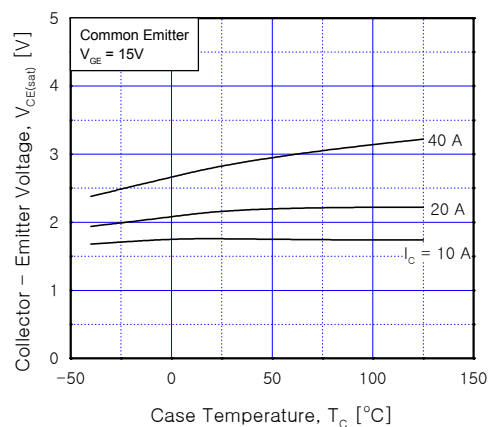


Figure 4. Transient Thermal Impedance

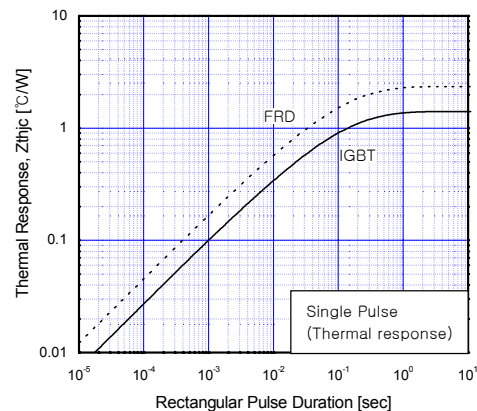


Figure 5. Saturation Voltage vs. V_{GE}

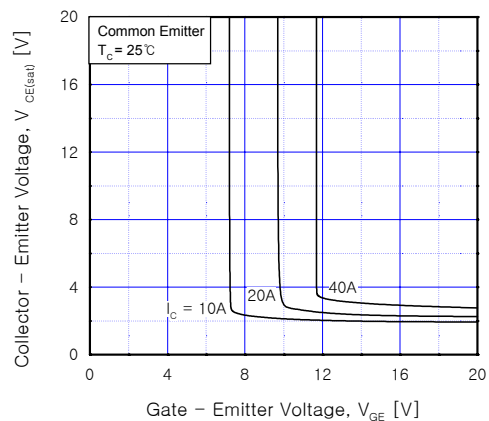
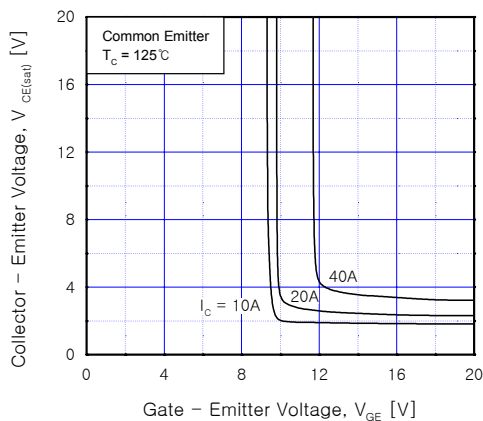


Figure 6. Saturation Voltage vs. V_{GE}



Typical Performance Characteristics (Continued)

Figure 7. Capacitance Characteristics

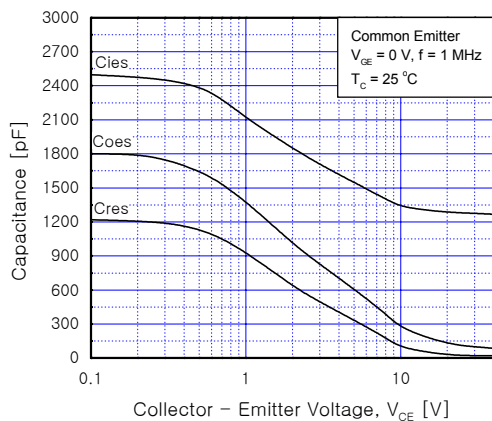


Figure 9. Turn-Off Characteristics vs. Gate Resistance

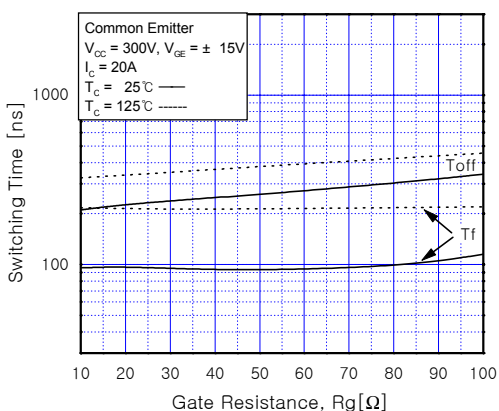


Figure 11. Turn-On Characteristics vs. Collector Current

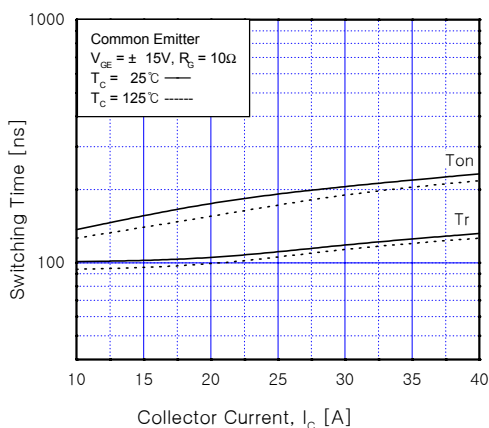


Figure 8. Turn-On Characteristics vs. Gate Resistance

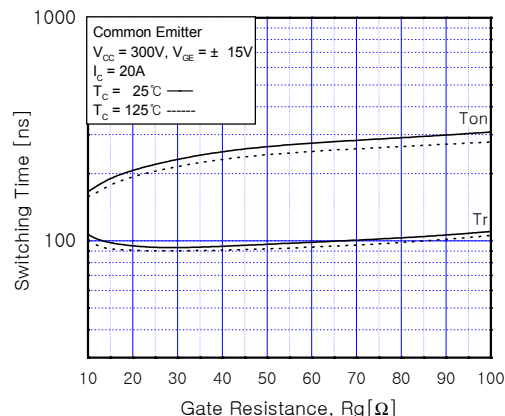


Figure 10. Switching Loss vs. Gate Resistance

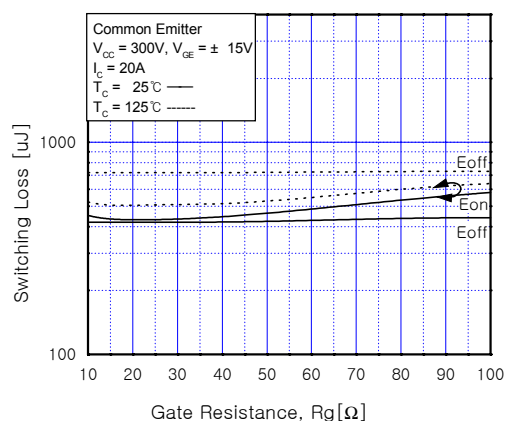
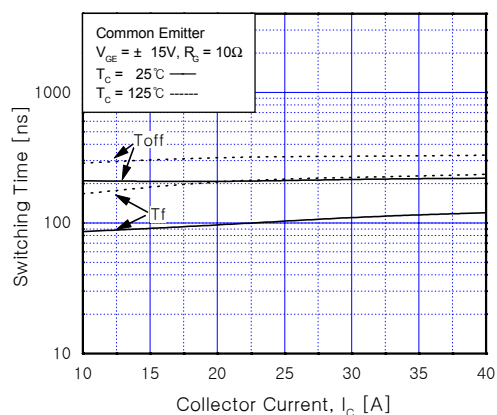


Figure 12. Turn-Off Characteristics vs. Collector Current



Typical Performance Characteristics (Continued)

Figure 13. Switching Loss vs. Collector Current

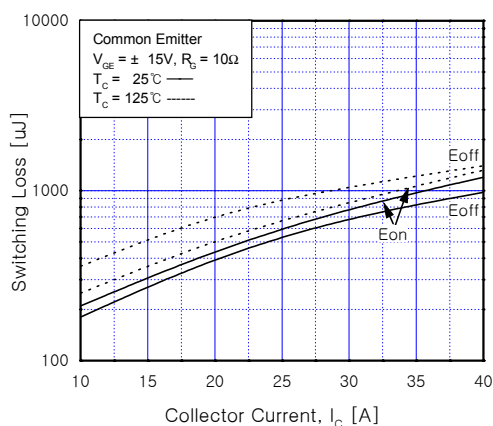


Figure 14. Gate Charge Characteristics

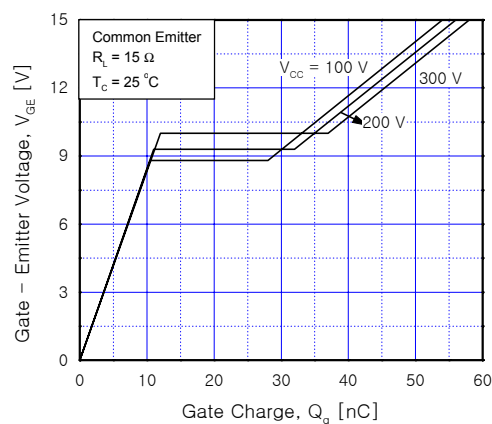


Figure 15. SOA Characteristics

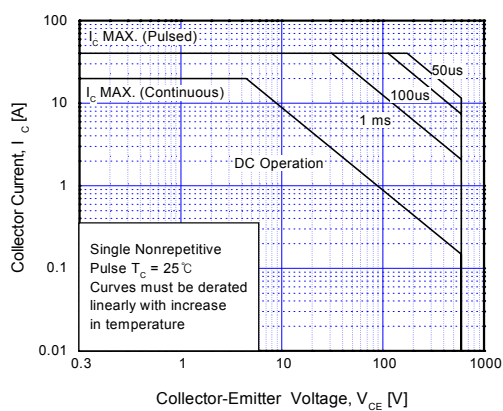


Figure 16. RBSOA Characteristics

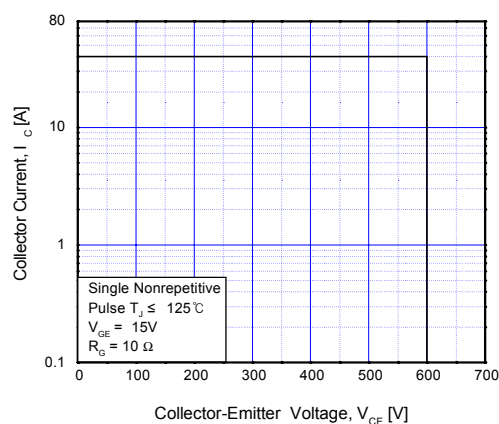


Figure 17. Forward Characteristics

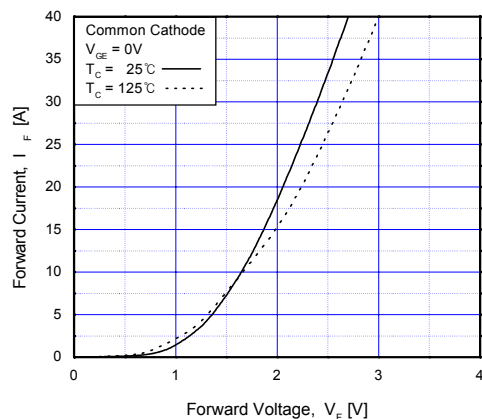
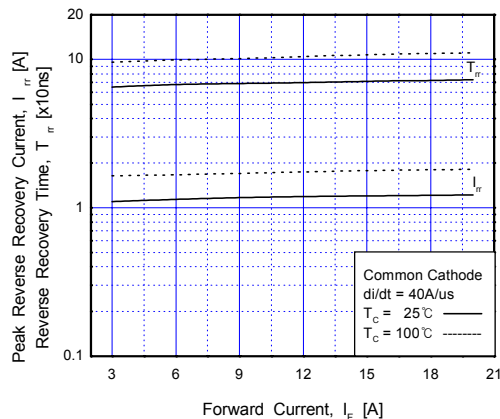
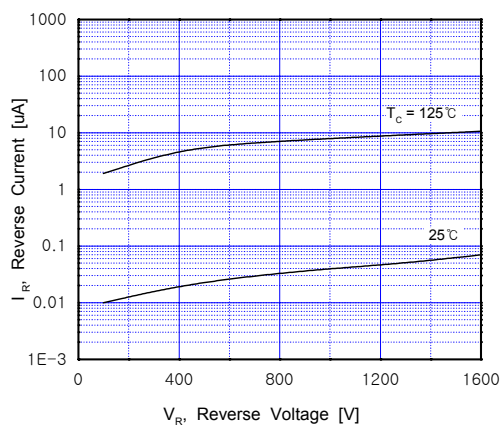
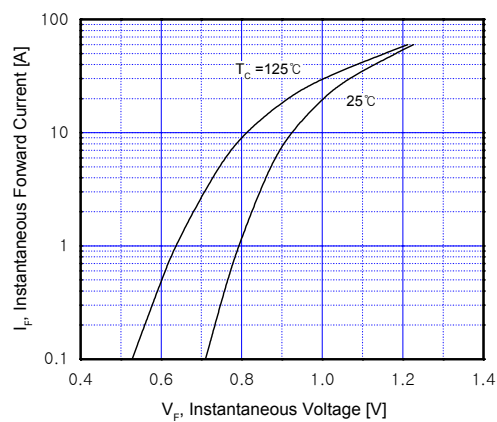
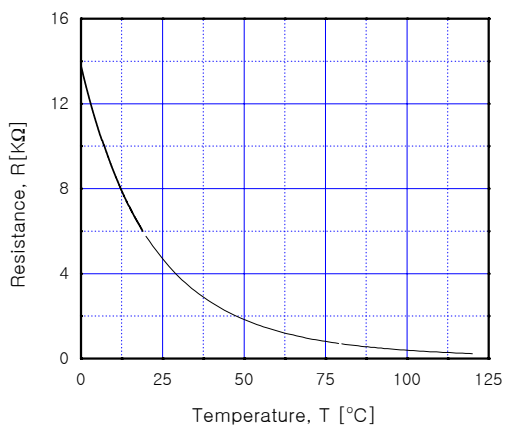


Figure 18. Reverse Recovery Characteristics

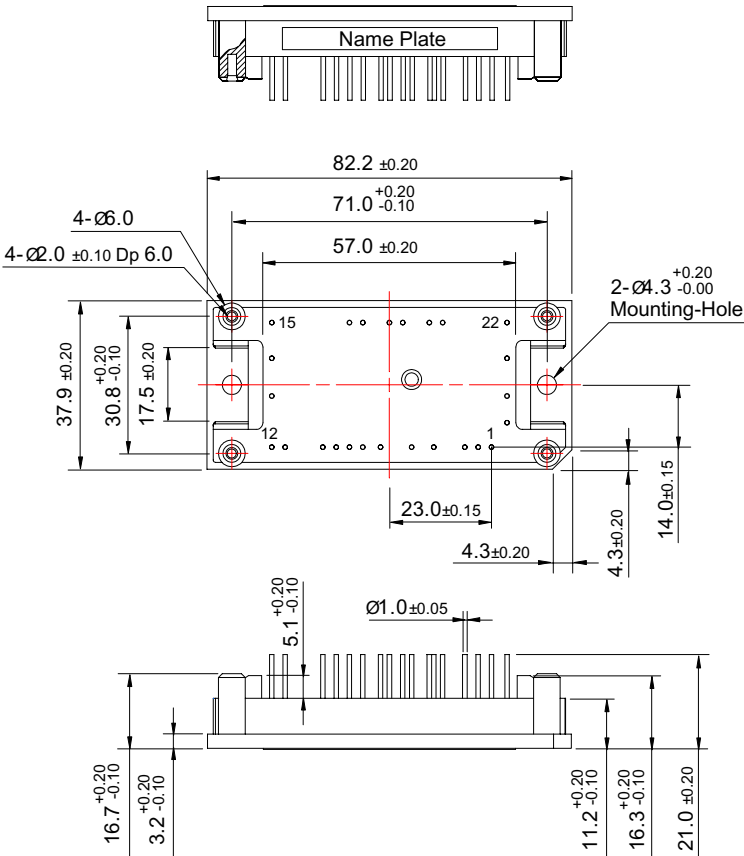


Typical Performance Characteristics (Continued)**Figure 19. Rectifier (Converter) Characteristics****Figure 20. Rectifier (Converter) Characteristics****Figure 21. NTC Characteristics**

Dimensions in Millimeters

Mechanical Dimensions

25PM-AA



-. Pin Coordinate

Pin #No	Coordinate	
	x	y
1	0.0	0.0
2	-3.0	0.0
3	-6.0	0.0
4	-13.0	0.0
5	-18.0	0.0
6	-25.0	0.0
7	-29.0	0.0
8	-32.0	0.0
9	-35.0	0.0
10	-38.0	0.0
11	-46.5	0.0
12	-49.5	0.0
13	-49.5	11.5
14	-49.5	20.0
15	-49.5	28.0
16	-32.0	28.0
17	-29.0	28.0
18	-23.0	28.0
19	-20.0	28.0
20	-14.0	28.0
21	-11.0	28.0
22	3.5	28.0
23	3.5	20.0
24	3.5	11.5
25	3.5	5.5

* datum pin : #1

* Pin Tilt : ±0.15

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